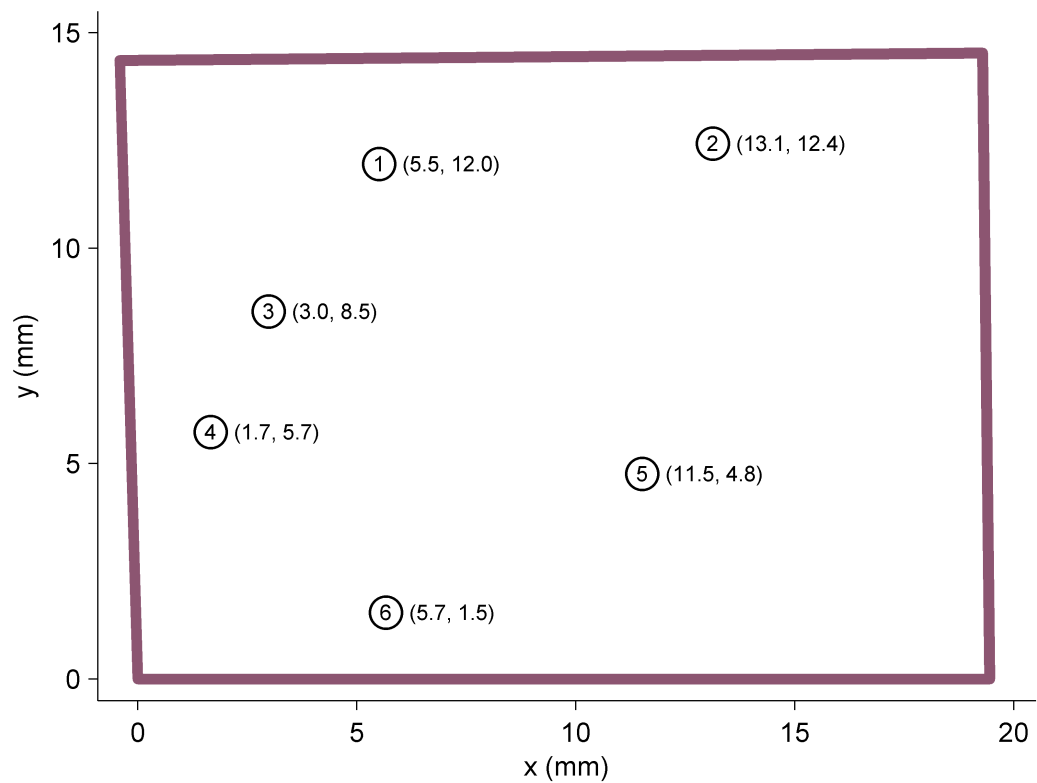


Sample S5520 Datasheet

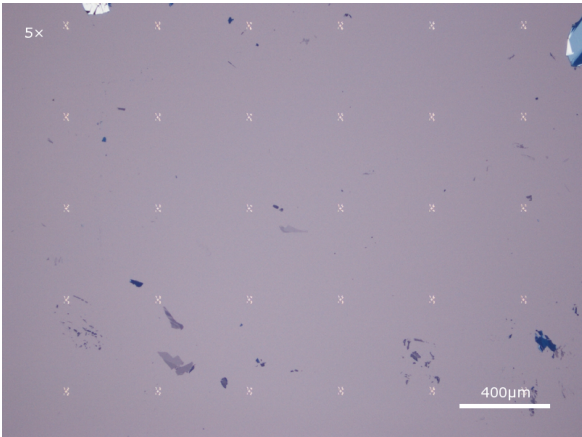
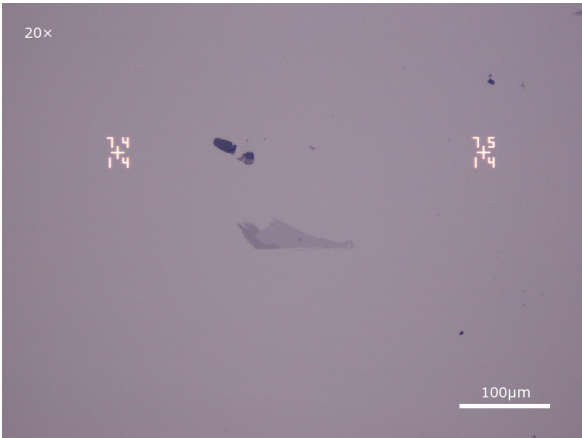
Parent Wafer

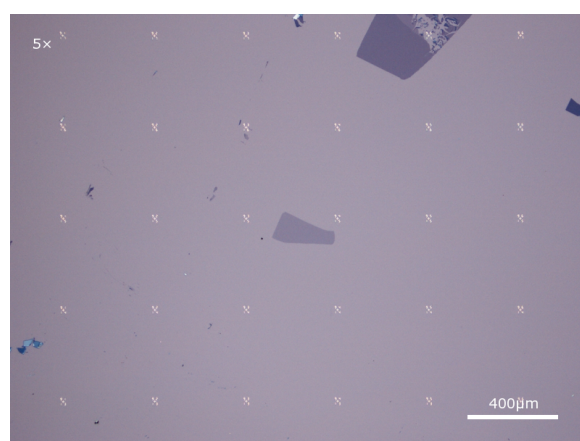
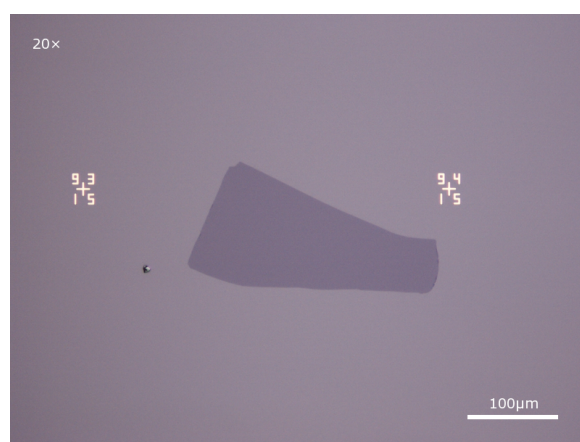
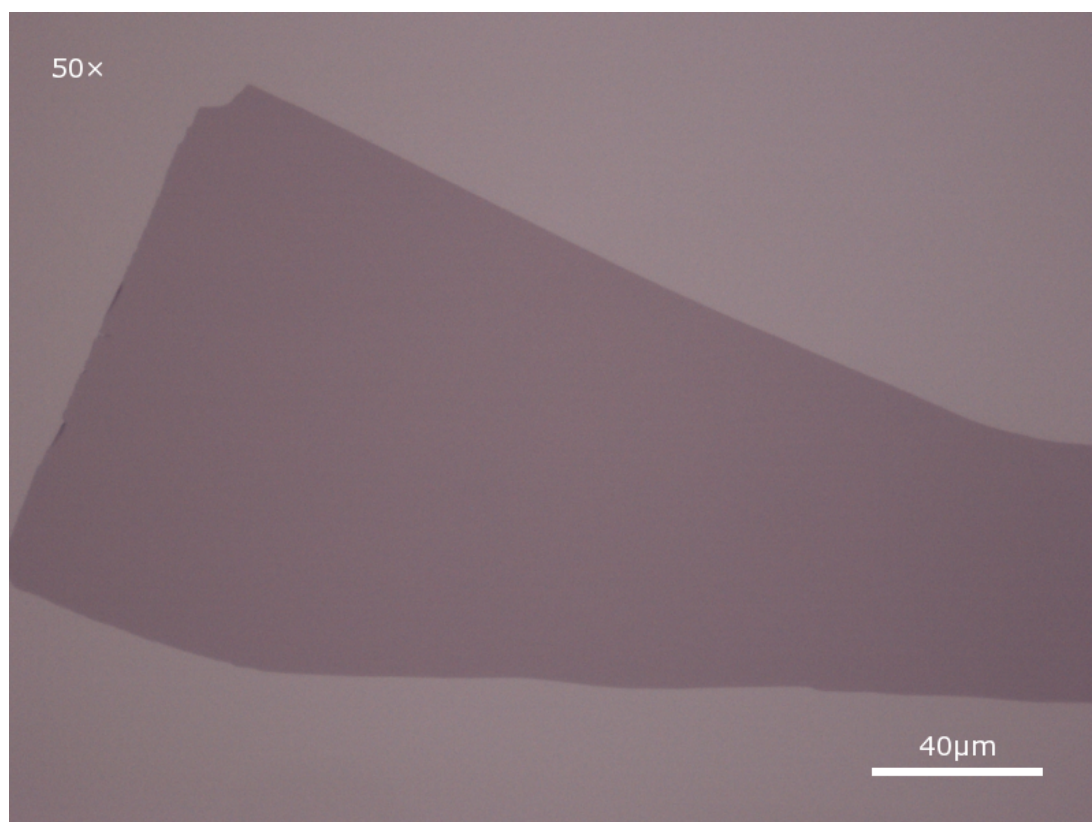
Supplier	IDB Technologies Ltd.
Diameter	100mm
Si Orientation	<100>
Si Thickness	525 μm
Si Doping	N-type, arsenic
Resistivity	0.001-0.010 Ωcm
Oxide	90 nm dry thermal oxide

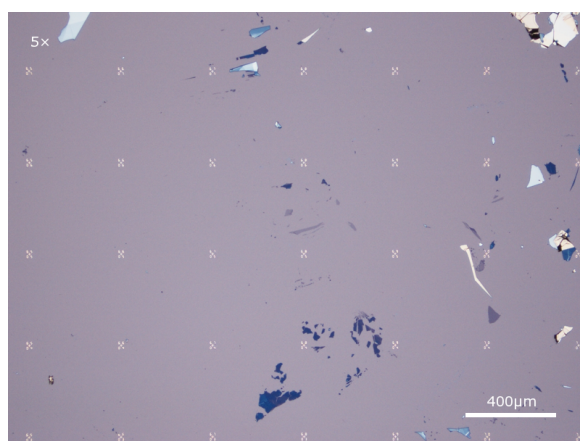
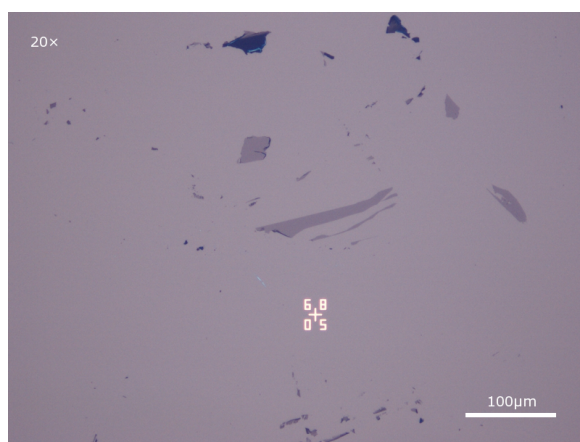
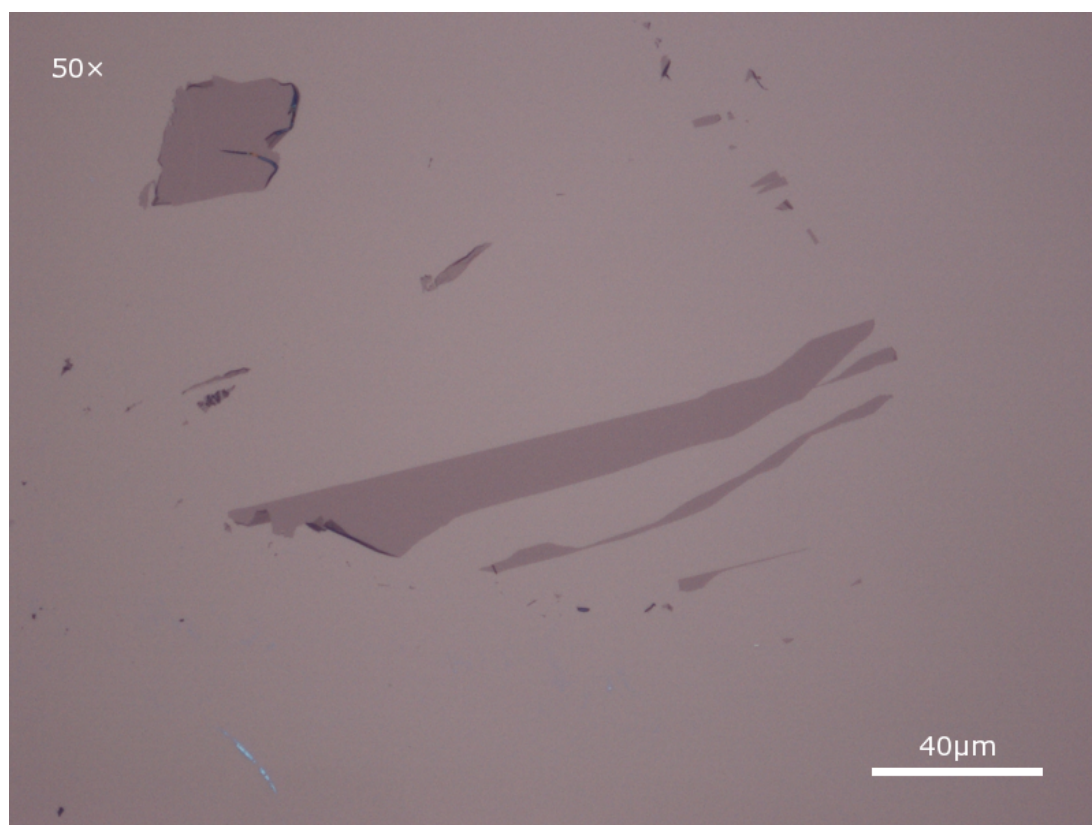
Substrate Map



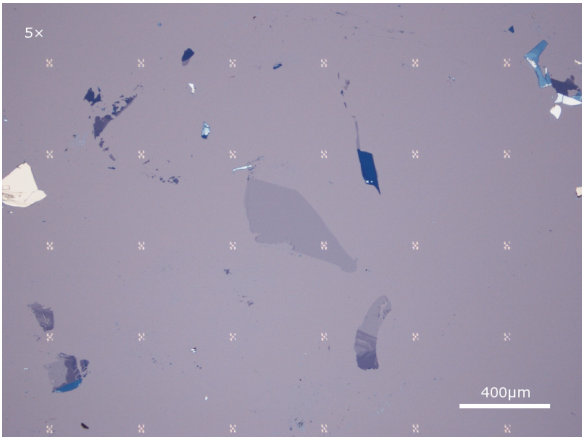
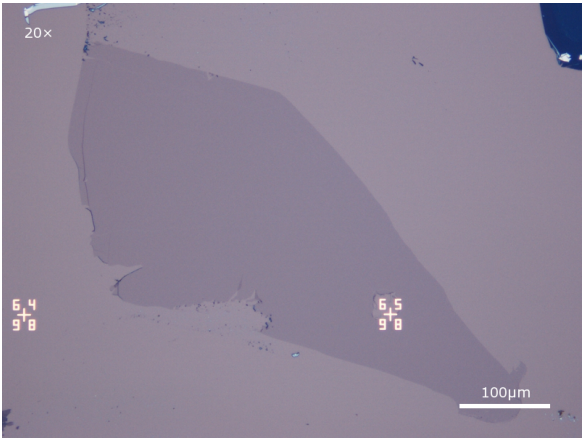
Flake 1 of 6: x=5.5mm, y=12.0mm, >1000 μm^2 monolayer region



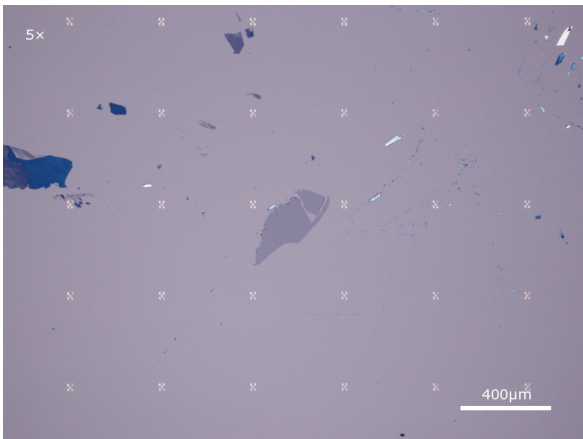
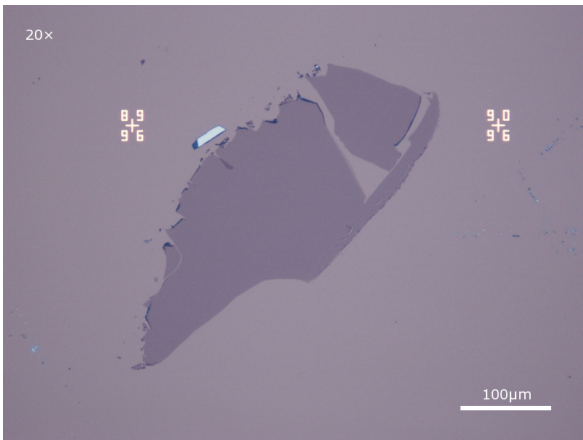
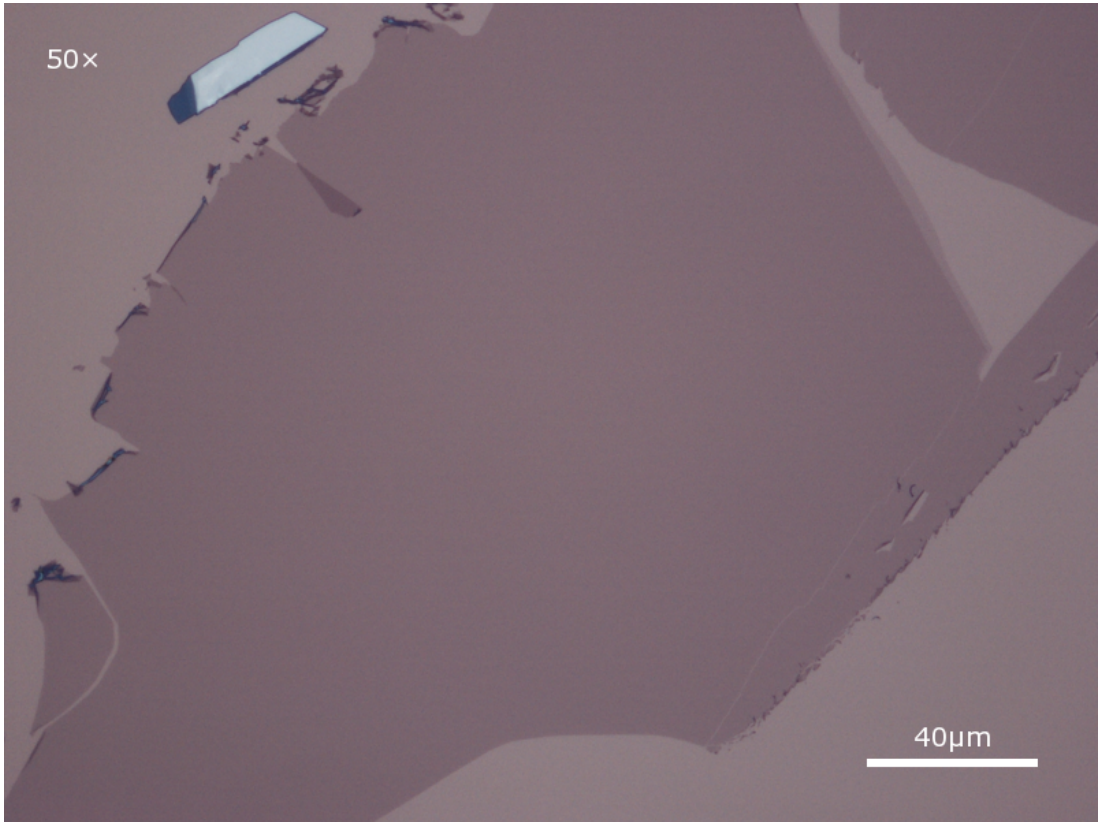
Flake 2 of 6: x=13.1mm, y=12.4mm, >20000 μm^2 bilayer flake

Flake 3 of 6: $x=3.0\text{mm}$, $y=8.5\text{mm}$, $>1000\text{ }\mu\text{m}^2$ bilayer flake

Flake 4 of 6: x=1.7mm, y=5.7mm, >80000 μm^2 monolayer flake



Flake 5 of 6: x=11.5mm, y=4.8mm, >25000 μm^2 bilayer flake



Flake 6 of 6: x=5.7mm, y=1.5mm, >3500 μm^2 monolayer region

